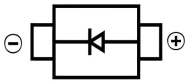
SMAF General Purpose Rectifier Diode 通用整流二极管





▪ Features 特点

Low reverse leakage current 低反向漏电流
High surge current capability 高浪涌电流能力
Built-in strain relief 内应力释放
Surface mount device 表面贴装器件
Case 封装:SMAF

▪ Maximum Rating 最大额定值

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	S1AF	S1BF	S1DF	S1GF	S1JF	S1KF	S1MF	Unit 单位
Marking 印字		S1AF	S1BF	S1DF	S1GF	S1JF	S1KF	S1MF	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	1							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	30							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	50							℃/W
Junction and Storage Temperature 结温和储藏温度	T_J,T_{stg}	150℃,-65to+150℃							

▪ Electrical Characteristics 电特性

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Test Condition 测试条件
Forward Voltage 正向电压	V_F		1.0	1.1	V	I_F=1A
Reverse Current(T_A=25℃/) 反向电流(T_A=100℃/)	I_R			5 50	uA	V_R=V_{RRM}
Diode Capacitance 二极管电容	C_D		15		pF	V_R=4V,f=1MHz

■ Typical Characteristic Curve 典型特性曲线

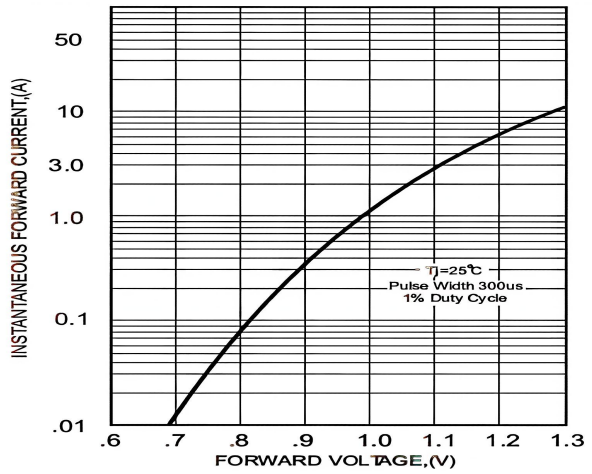


Figure 1: Forward Characteristics

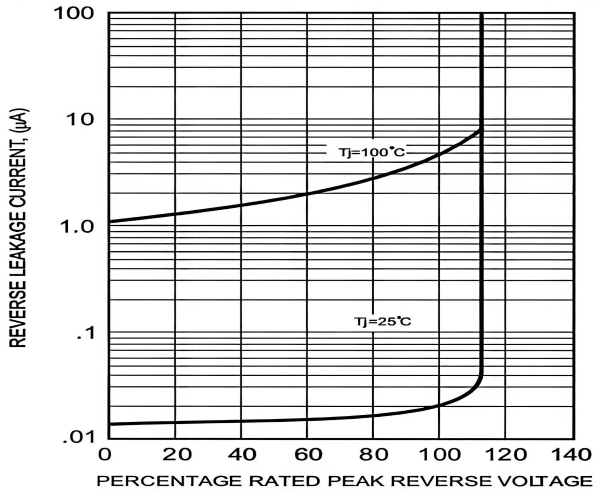


Figure 2: Reverse Characteristics

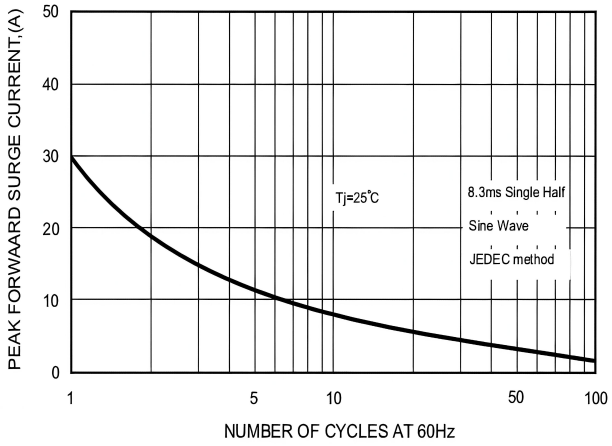


Figure 3:Surge Current Characteristics

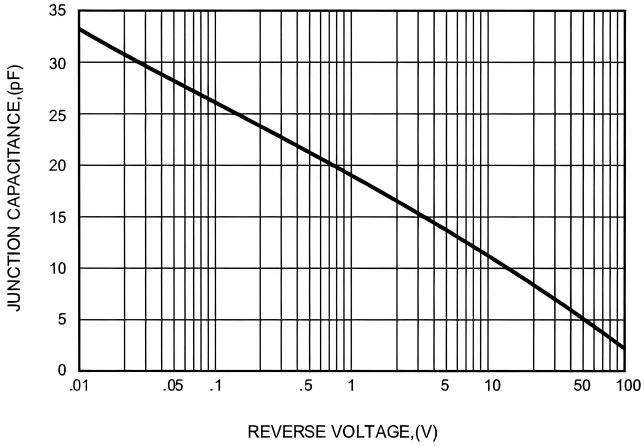


Figure 4: Junction Capacitance

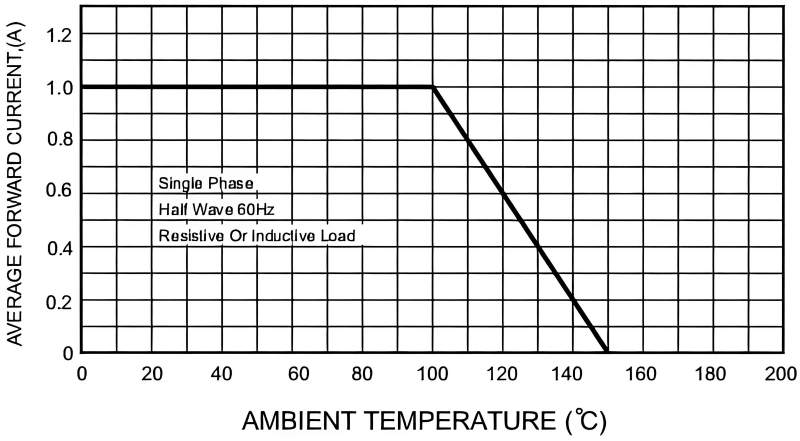
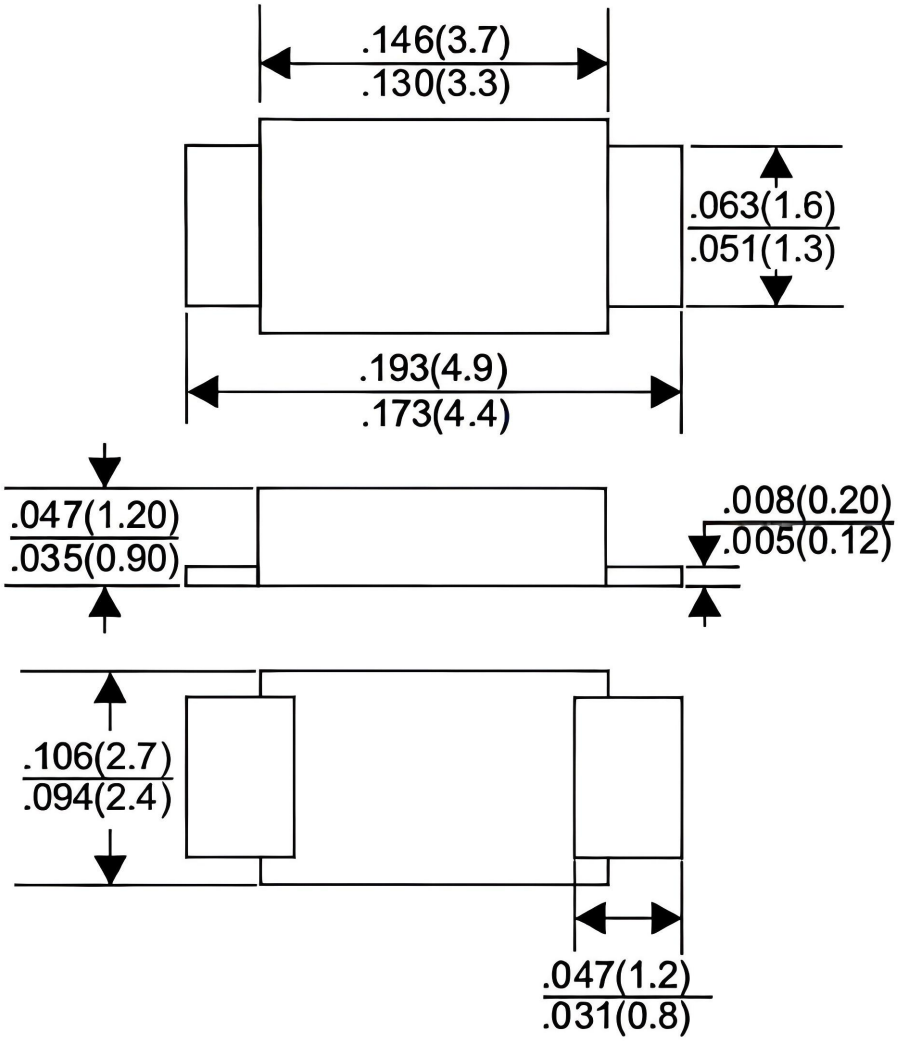


Figure 5: Forward Current Derating

■ **Dimension 外形封装尺寸**



Dimensions in inches and (millimeters)